



TO-126 Plastic-Encapsulate Transistors

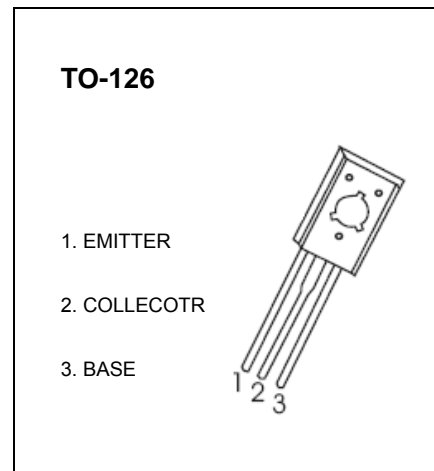
BD434,436 TRANSISTOR (PNP)

FEATURES

- Amplifier and Switching Applications

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{CBO}	Collector-Base Voltage	BD434	-22	V
		BD436	-32	
V _{CEO}	Collector-Emitter Voltage	BD434	-22	V
		BD436	-32	
V _{EBO}	Emitter-Base Voltage		-5	V
I _C	Collector Current –Continuous		-4	A
P _C	Collector Power Dissipation		1.25	W
T _J	Junction Temperature		150	°C
T _{stg}	Storage Temperature		-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	BD434	-22		V	
			BD436	-32			
Collector-emitter breakdown voltage	V _{CEO} ^{(SUS)(1)}	I _C =-100mA, I _B =0	BD434	-22		V	
			BD436	-32			
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V	
Collector cut-off current	I _{CBO}	V _{CB} =-22V, I _E =0	BD434			-100	μA
		V _{CB} =-32V, I _E =0	BD436				
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-1	mA	
DC current gain	h _{FE(1)} ⁽¹⁾	V _{CE} =-5V, I _C =-10mA	40				
	h _{FE(2)} ⁽¹⁾	V _{CE} =-1V, I _C =-500mA	85		375		
	h _{FE(3)} ⁽¹⁾	V _{CE} =-1V, I _C =-2A	50				
Collector-emitter saturation voltage	V _{CE(sat)} ⁽¹⁾	I _C =-2A, I _B =-0.2A			-0.5	V	
Base-emitter voltage	V _{BE} ⁽¹⁾	V _{CE} =-1V, I _C =-2A			-1.1	V	
Transition frequency	f _T	V _{CE} =-1V, I _C =-250mA	3			MHz	

⁽¹⁾Pulse test.